Advanced Product Information June 2002 (1 of 2)

## Features

$\square$ Low-Noise Figure from 0.8 to 2.0 GHz
$\square$ High Gain
$\square$ High Intercept Point

- Highly Stable
- Easily Matched to $50 \Omega$
$\square 70 \mathrm{mil}$ Package
- PHEMT Material


## Applications

- Cellular Base Stations
$\square$ PCS Base Stations
Industrial Data Networks


## Description

Celeritek's CFB0303 is a high performance GaAs PHEMT with $600 \mu \mathrm{~m}$ gate width and $0.25 \mu \mathrm{~m}$ gate length. The low noise figure and high intercept point of this device makes it well suited for use as the low-noise amplifier of the

## High Dynamic Range Low-Noise GaAs FET


base station receiver in PCS, Japanese PHS, AMPS, GSM and other communications systems. The CFB0303 is in an indus-try-standard 70 mil package. It is surface mountable and available in tape and reel.

Electrical Specifications (TA $=25^{\circ} \mathrm{C}, 2 \mathrm{GHz}$ )

| Parameters | Conditions | Min | Typ | Max | Units |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{d}}=4 \mathrm{~V}, \mathrm{I}_{\mathrm{d}}=75 \mathrm{~mA}$ |  |  |  |  |  |
| Noise Figure ${ }^{2}$ |  |  | 0.5 | 0.6 | dB |
| Associated Gain ${ }^{2}$ | @ Noise Figure | 19.0 | 20.0 | 22.7 | dB |
| $\mathrm{P}_{\text {out }} 1,3$ | $\mathrm{P}_{-1}$ | 20.0 | 21.0 | 22.0 | dBm |
| $\mathrm{IP}_{3}{ }^{3}$ | $+5 \mathrm{dBm} \mathrm{P} \mathrm{OUT}^{\text {/Tone }}$ | 32 | 34 |  | dBm |
| $\mathrm{I}_{\mathrm{d}}{ }^{3}$ | @ P-1 |  | 83 |  | mA |
| Transconductance | $\mathrm{V}_{\mathrm{ds}}=4 \mathrm{~V}, \mathrm{~V}_{\mathrm{gs}}=0 \mathrm{~V}$ |  | 350 |  | mho |
| Saturated Drain Current | $\mathrm{V}_{\mathrm{ds}}=4 \mathrm{~V}, \mathrm{~V}_{\mathrm{gs}}=0 \mathrm{~V}$ | 80 | 140 | 240 | mA |
| Pinchoff Voltages | $\mathrm{V}_{\mathrm{ds}}=4 \mathrm{~V}, \mathrm{I}_{\mathrm{ds}}=1 \mathrm{~mA}$ |  | -0.3 |  | V |
| Thermal Resistance | @ $\mathrm{T}_{\text {case }}=150^{\circ} \mathrm{C}$ liquid crystal test |  | 200 |  | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

Notes: 1. @ $\mathrm{T}_{\text {case }}=25^{\circ} \mathrm{C}$. Derate $5 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ for $\mathrm{T}_{\text {case }}>25^{\circ} \mathrm{C}$.
2. Input matched for low noise.
3. Matched for power transfer.

Typical Scattering Parameters $\left(\mathrm{TA}=25^{\circ} \mathrm{C}, \mathrm{V}_{\mathrm{DS}}=4 \mathrm{~V}, \mathrm{I}_{\mathrm{DS}}=75 \mathrm{~mA}\right)$

| Frequency (GHz) | $\mathrm{S}_{11}$ |  | $\mathrm{S}_{21}$ |  | $\mathrm{S}_{12}$ |  | $\mathrm{S}_{22}$ |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | Mag | Ang | Mag (dB) | Ang | MAG (dB) | ANG | MAG | ANG |
| 0.5 | 0.98 | -24 | 8.47 | 160 | 0.02 | 77 | 0.33 | -9 |
| 1.0 | 0.94 | -44 | 8.20 | 147 | 0.03 | 69 | 0.32 | -15 |
| 2.0 | 0.85 | -80 | 7.30 | 118 | 0.05 | 51 | 0.27 | -36 |
| 3.0 | 0.76 | -112 | 6.30 | 94 | 0.07 | 37 | 0.25 | -50 |
| 4.0 | 0.70 | -134 | 5.60 | 74 | 0.08 | 29 | 0.24 | -55 |
| 5.0 | 0.64 | -154 | 5.13 | 54 | 0.09 | 19 | 0.23 | -61 |


| $\begin{aligned} & \text { Frequency } \\ & \text { (GHz) } \end{aligned}$ | $\mathrm{F}_{\left(\mathrm{dB} \mathrm{di}^{2}\right.} 1$ | Gamma Opt |  | Rn/50 |
| :---: | :---: | :---: | :---: | :---: |
|  |  | Mag | Ang |  |
| 0.8 | 0.4 | 0.6 | 27 | 0.19 |
| 1.0 | 0.4 | 0.6 | 29 | 0.17 |
| 1.2 | 0.4 | 0.6 | 32 | 0.18 |
| 1.4 | 0.4 | 0.6 | 35 | 0.18 |
| 1.6 | 0.4 | 0.5 | 38 | 0.17 |
| 1.8 | 0.4 | 0.5 | 41 | 0.16 |
| 2.0 | 0.5 | 0.5 | 45 | 0.15 |
| 2.2 | 0.5 | 0.5 | 49 | 0.15 |
| 2.4 | 0.5 | 0.5 | 54 | 0.14 |
| 2.6 | 0.5 | 0.5 | 60 | 0.13 |

Note: 1. Fmin values reflect the circuit losses in the test fixture when matched to optimum noise figure.

Absolute Maximum Ratings

| Parameter | Symbol | Rating |
| :--- | :---: | :---: |
| Drain-Source Voltage | $\mathrm{V}_{\mathrm{ds}}$ | +8 V |
| Gate-Source Voltage | $\mathrm{V}_{\mathrm{gs}}$ | -5 V |
| Drain Current | $\mathrm{I}_{\mathrm{ds}}$ | Idss |
| Continuous Dissipation ${ }^{1}$ | Pt | 750 mW |
| Channel Temperature | Tch | $175^{\circ} \mathrm{C}$ |
| Storage Temperature | Tstg | $-65^{\circ} \mathrm{C}$ to $+150^{\circ} \mathrm{C}$ |

## Notes

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